



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Transistors

MMST2907A TRANSISTOR (PNP)

FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available(MMST2222A)

MARKING:K3F

MAXIMUM RATINGS($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.6	A
P_C	Collector Dissipation	0.2	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55 to +150	$^{\circ}\text{C}$

SOT-323



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$			-100	nA
Collector cut-off current	I_{CES}	$V_{CB}=-30\text{V}, I_B=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3\text{V}, I_C=0$			-100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=-10\text{V}, I_C=-0.1\text{mA}$	75			
	$h_{FE(2)}$	$V_{CE}=-10\text{V}, I_C=-1\text{mA}$	100			
	$h_{FE(3)}$	$V_{CE}=-10\text{V}, I_C=-10\text{mA}$	100			
	$h_{FE(4)}$	$V_{CE}=-10\text{V}, I_C=-150\text{mA}$	100		300	
	$h_{FE(5)}$	$V_{CE}=-10\text{V}, I_C=-500\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-150\text{mA}, I_B=-15\text{mA}$			-0.4	V
	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-150\text{mA}, I_B=-15\text{mA}$	-0.6		-1.3	V
	$V_{BE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-2.6	V
Transition frequency	f_T	$V_{CE}=-20\text{V}, I_C=-50\text{mA}, f=100\text{MHz}$	200			MHz
Output capacitance	C_{obo}	$V_{CB}=-10\text{V}, I_E=0, f=0.1\text{MHz}$			8	pF
Input capacitance	C_{ib}	$V_{EB}=-2\text{V}, I_C=0, f=0.1\text{MHz}$			30	pF
Delay time	t_d	$V_{CC}=-30\text{V}, V_{BE(off)}=-1.5\text{V}, I_C=-150\text{mA}$			10	nS
Rise time	t_r	$I_{B1}=-15\text{mA}$			40	nS
Storage time	t_s	$V_{CC}=-30\text{V}, I_C=-150\text{mA}, I_{B1}=-I_{B2}=-15\text{mA}$			80	nS
Fall time	t_f				30	nS

Typical Characteristics

MMST2907A

●Electrical characteristic curves

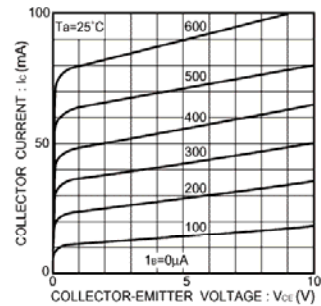


Fig.1 Grounded emitter output characteristics

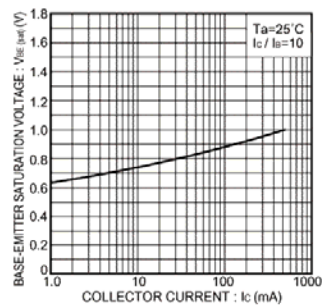


Fig.2 Base-emitter saturation voltage vs. collector current

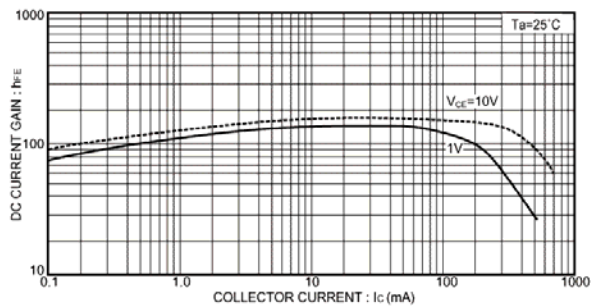


Fig.3 DC current gain vs. collector current (I)

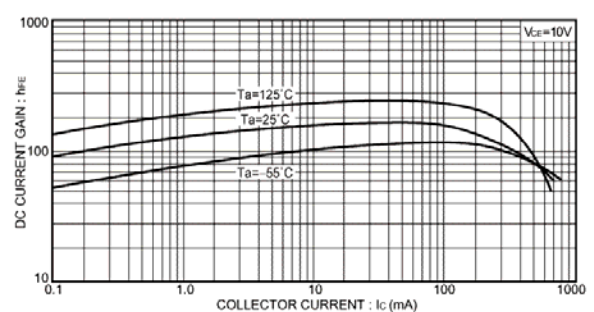


Fig.4 DC current gain vs. collector current (II)

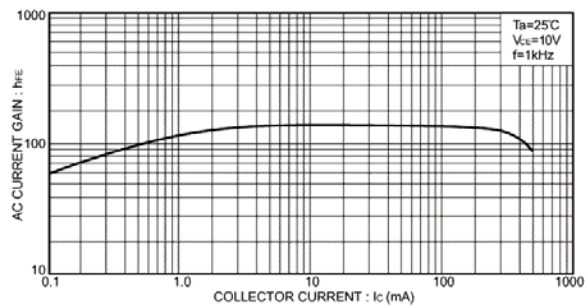


Fig.5 AC current gain vs. collector current

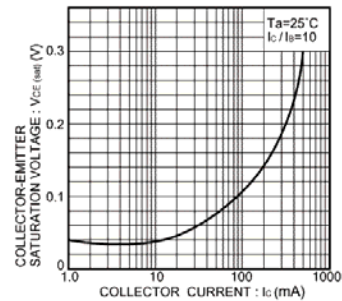


Fig.6 Collector-emitter saturation voltage vs. collector current

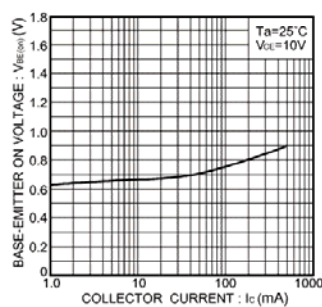


Fig.7 Grounded emitter propagation characteristics

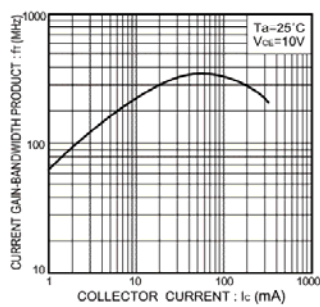


Fig.8 Gain bandwidth product vs. collector current

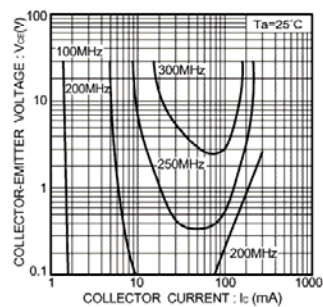


Fig.9 Gain bandwidth product

Typical Characteristics

MMST2907A

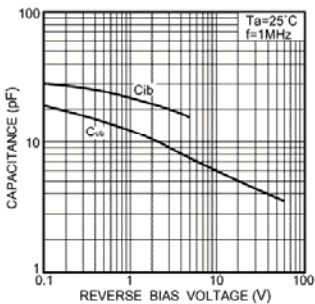


Fig.10 Input/output capacitance vs. voltage

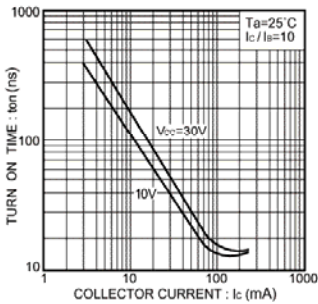


Fig.11 Turn-on time vs.collector current

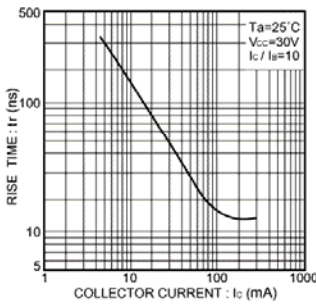


Fig.12 Rise time vs. collector current

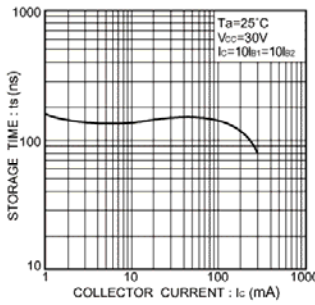


Fig.13 Storage time vs. collector current

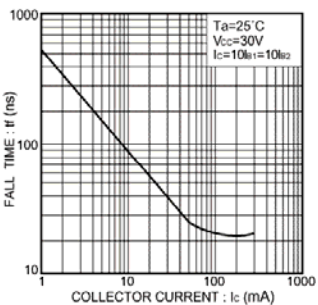


Fig.14 Fall time vs. collector current